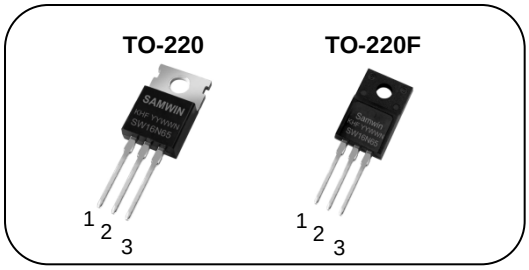
N-channel TO-220 /TO-220F MOSFET

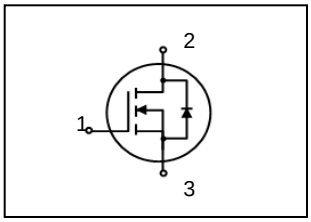
Features

- High ruggedness
- $R_{DS(ON)}$ (Max0.25Ω)@V_{GS}=10V
- Gate Charge (Typical 43nC)
- Improved dv/dt Capability
- 100% Avalanche Tested



1. Gate 2. Drain 3. Source

BV_{DSS} : 650V
I_D : 16A
$R_{DS(ON)}$:0.25Ω



General Description

This power MOSFET is produced with advanced super-junction technology of SAMWIN. This technology enable power MOSFET to have better characteristics, such as fast switching time, excellent avalanche characteristics, low gate charge and especially in low on resistance. This power MOSFET is usually used at high efficient DC to DC converter block and switch mode power supply.

Order Codes

Item	Sales Type	Marking	Package	Packaging
1	SW P 16N65K	SW16N65K	TO-220	TUBE
2	SW F 16N65K	SW16N65K	TO-220F	TUBE

Absolute maximum ratings

Symbol	Parameter		Value		Unit
			TO-220	TO-220F	
V_{DSS}	Drain to Source Voltage		650		V
I_D	Continuous Drain Current (@T_C=25°C)		16*		A
	Continuous Drain Current (@T_C=100°C)		10.1*		A
I_{DM}	Drain current pulsed	(note 1)	64		A
V_{GS}	Gate to Source Voltage		±30		V
E_{AS}	Single pulsed Avalanche Energy	(note 2)	300		mJ
E_{AR}	Repetitive Avalanche Energy	(note 1)	16		mJ
dv/dt	Peak diode Recovery dv/dt	(note 3)	5		V/ns
P_D	Total power dissipation (@T_C=25°C)		271.7	32.2	W
	Derating Factor above 25°C		2.2	0.26	W/°C
T_{STG}, T_J	Operating Junction Temperature & Storage Temperature		-55 ~ + 150		°C
T_L	Maximum Lead Temperature for soldering purpose, 1/8 from Case for 5 seconds.		300		°C

*. Drain current is limited by junction temperature.

Thermal characteristics

Symbol	Parameter	Value		Unit
		TO-220	TO-220F	
R_{thjc}	Thermal resistance, Junction to case	0.46	3.88	°C/W
R_{thcs}	Thermal resistance, Case to Sink			°C/W
R_{thja}	Thermal resistance, Junction to ambient	55.4	45.1	°C/W

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Electrical characteristic (T_C = 25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
Off characteristics						
BV_{DSS}	Drain to source breakdown voltage	V_{GS}=0V, I_D=250uA	650			V
ΔBV_{DSS} / ΔT_J	Breakdown voltage temperature coefficient	I_D=250uA, referenced to 25°C		0.67		V/°C
I_{DSS}	Drain to source leakage current	V_{DS}=650V, V_{GS}=0V			1	uA
		V_{DS}=520V, T_C=125°C			50	uA
I_{GSS}	Gate to source leakage current, forward	V_{GS}=30V, V_{DS}=0V			100	nA
	Gate to source leakage current, reverse	V_{GS}=-30V, V_{DS}=0V			-100	nA
On characteristics						
$V_{GS(TH)}$	Gate threshold voltage	V_{DS}=V_{GS}, I_D=250uA	2	3.7	5	V
$R_{DS(ON)}$	Drain to source on state resistance	V_{GS}=10V, I_D = 8A		0.23	0.25	Ω
Gfs	Forward Transconductance	V_{DS} = 30V, I_D =8A	9			S
Dynamic characteristics						
C_{iss}	Input capacitance	V_{GS}=0V, V_{DS}=25V, f=1MHz		1510		pF
C_{oss}	Output capacitance			1080		
C_{rss}	Reverse transfer capacitance			20		
$t_{d(on)}$	Turn on delay time	V_{DS}=325V, I_D=16A, R_G=25Ω (note 4, 5)		21		ns
tr	Rising time			48		
$t_{d(off)}$	Turn off delay time			77		
t_f	Fall time			35		
Q_g	Total gate charge	V_{DS}=520V, V_{GS}=10V, I_D=16A (note 4, 5)		43		nC
Q_{gs}	Gate-source charge			13		
Q_{gd}	Gate-drain charge			19		

Source to drain diode ratings characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_S	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			16	A
I_{SM}	Pulsed source current				64	A
V_{SD}	Diode forward voltage drop.	I_S=16A, V_{GS}=0V			1.26	V
T_{rr}	Reverse recovery time	I_S=16A, V_{GS}=0V, dI_F/dt=100A/us		347		ns
Q_{rr}	Reverse recovery Charge			5.6		uC

※. Notes
1. Repeatitive rating : pulse width limited by junction temperature.
2. L = 37.5mH, I_{AS} = 4A, V_{DD} = V, R_G=25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 16A, di/dt = 100A/us, V_{DD} ≤ BV_{DSS}, Staring T_J =25°C
4. Pulse Test : Pulse Width ≤ 300us, duty cycle ≤ 2%
5. Essentially independent of operating temperature.

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Fig. 1. On-state characteristics

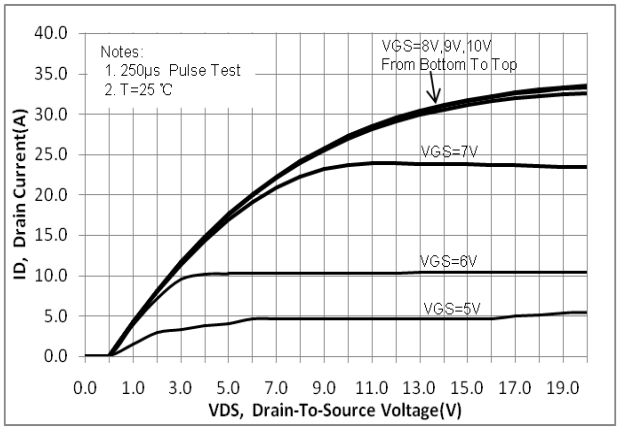


Fig. 2. On-resistance variation vs. drain current and gate voltage

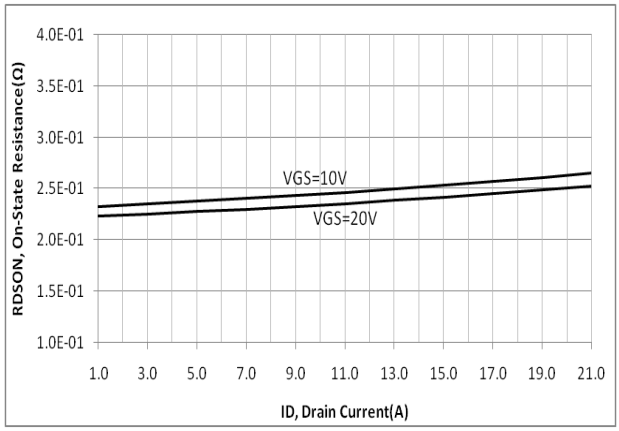


Fig. 3. Gate charge characteristics

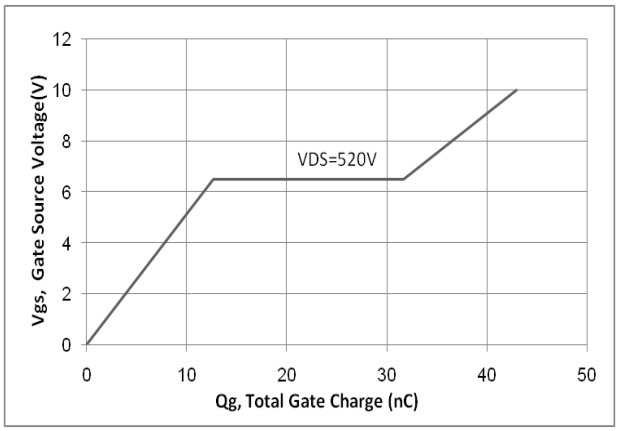


Fig. 4. On state current vs. diode forward voltage

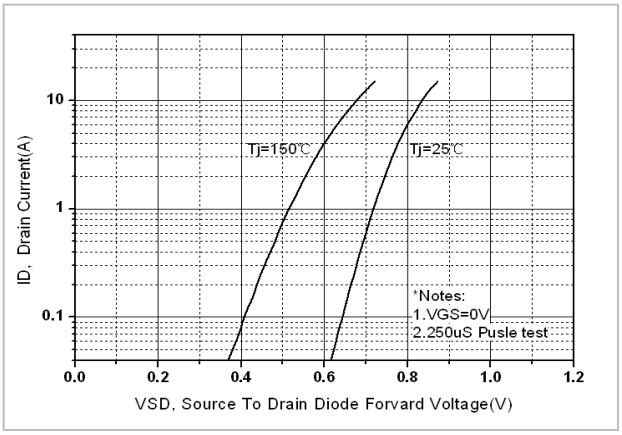


Fig 5. Breakdown Voltage Variation vs. Junction Temperature

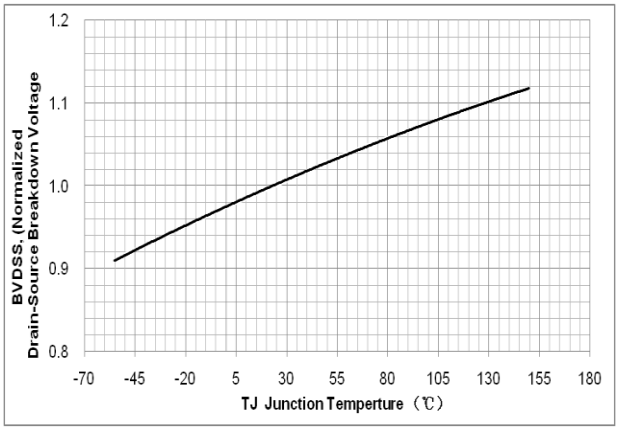
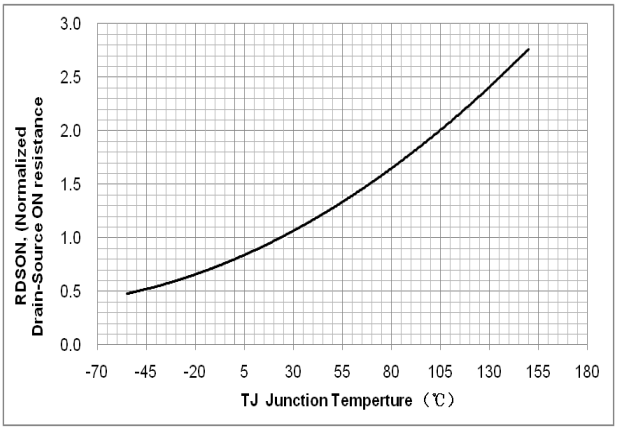


Fig. 6. On resistance variation vs. junction temperature



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Fig. 7. Maximum safe operating area（TO-220）

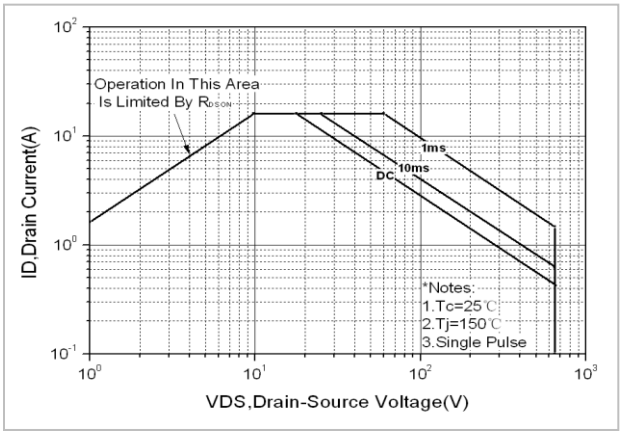


Fig. 8. Transient thermal response curve（TO-220）

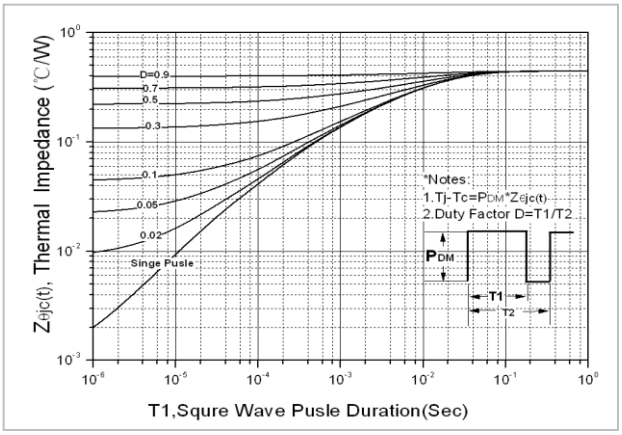


Fig. 9. Maximum safe operating area（TO-220F）

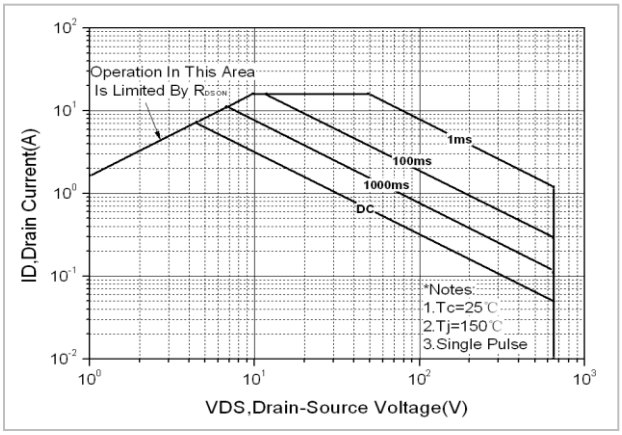


Fig. 10. Transient thermal response curve（TO-220F）

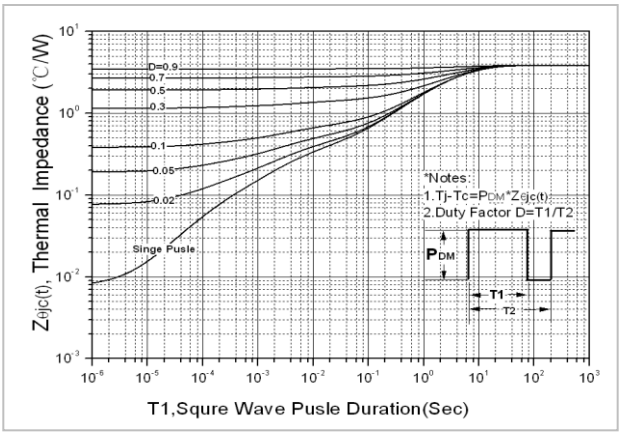
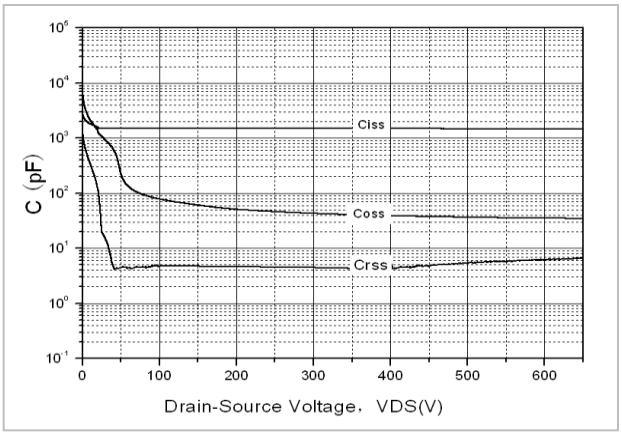


Fig. 11. Capacitance Characteristics



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Fig. 12. Gate charge test circuit & waveform

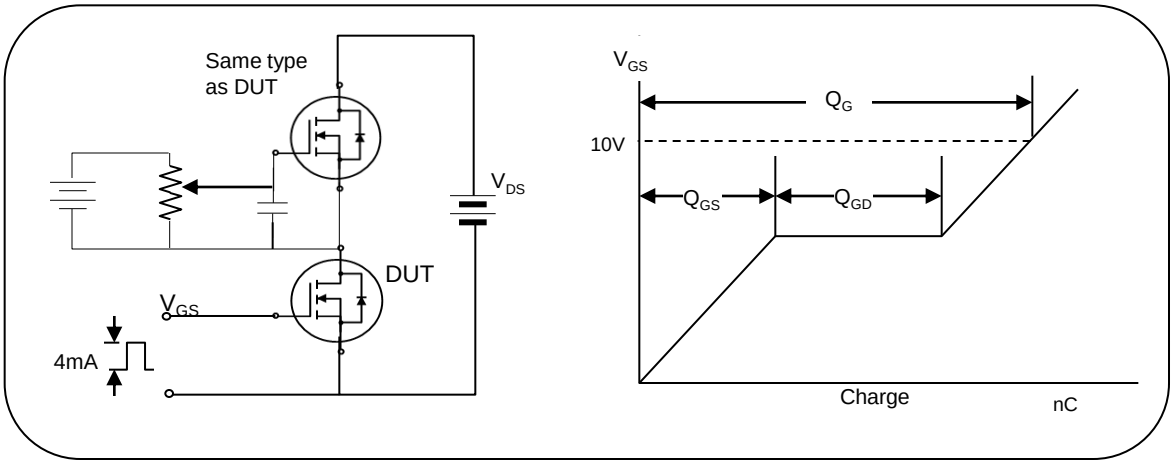


Fig. 13. Switching time test circuit & waveform

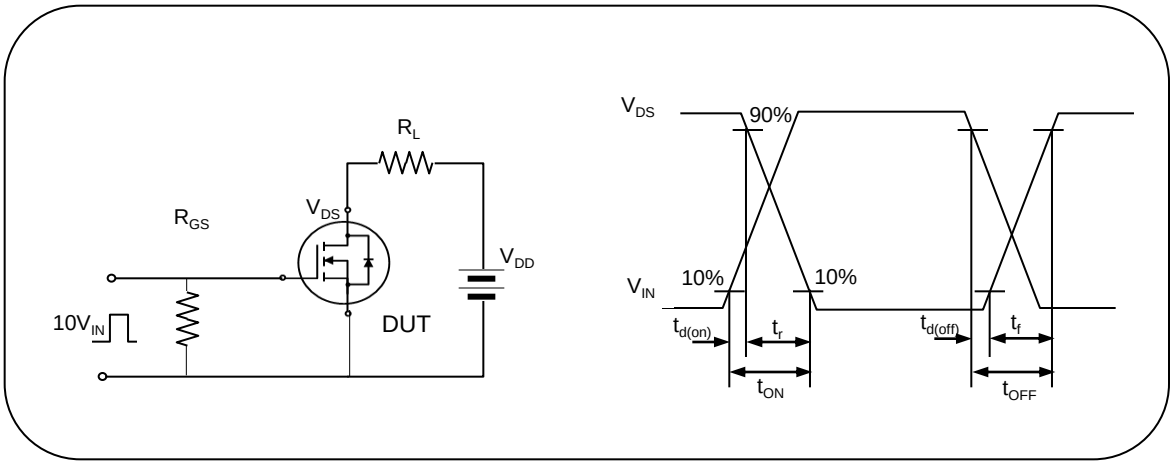
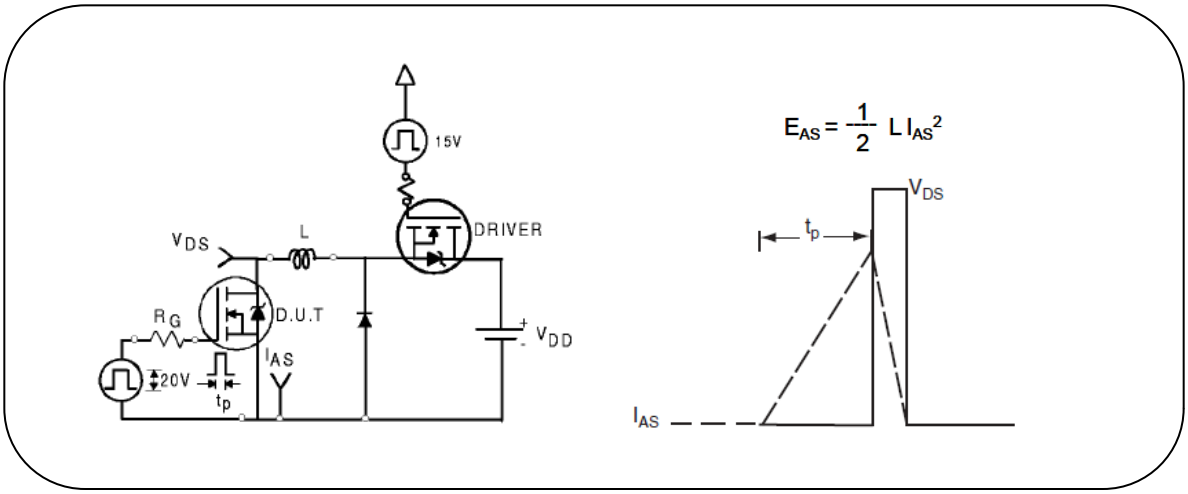
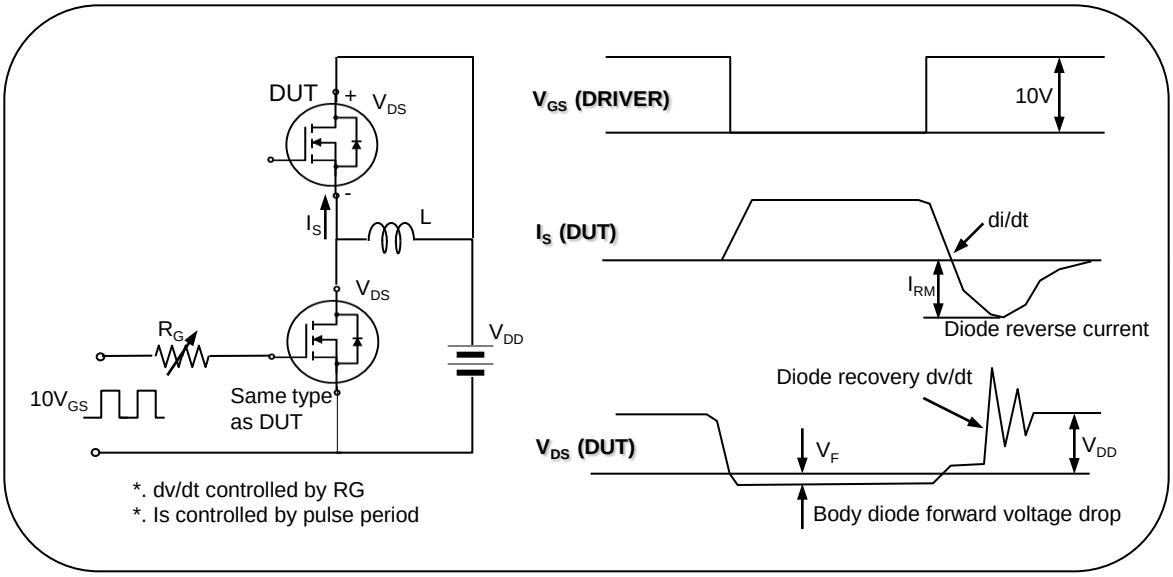


Fig. 14. Unclamped Inductive switching test circuit & waveform



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Fig. 15. Peak diode recovery dv/dt test circuit & waveform



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